

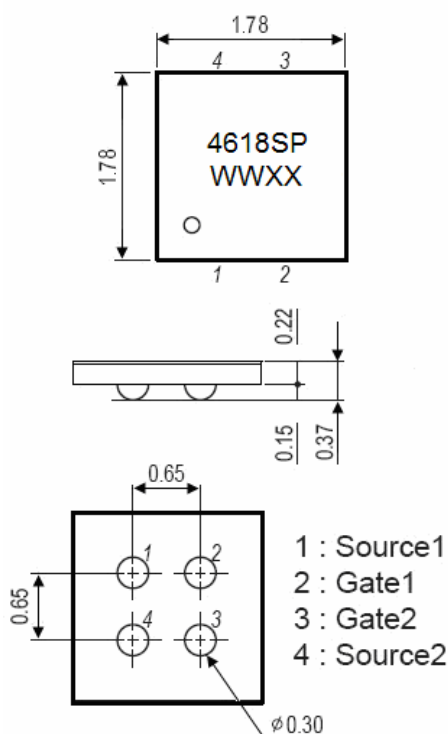
## NCE Common-Drain Dual N-Channel Enhancement Mode Field Effect Transistor

### Description

The NCE4618SP uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V while retaining a 12V  $V_{GS(MAX)}$  rating. It is ESD protected. This device is suitable for use as a unidirectional or bi-directional load switch, facilitated by its common-drain configuration.

### Package Dimensions

Unit : mm



### General Features

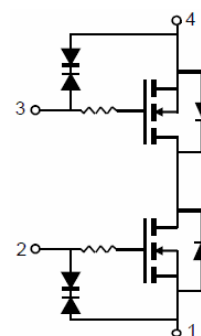
- $V_{SSS} = 20V, I_s = 6A$
- 2.5V drive
- Common-drain type
- 2KV HBM

### Package Information

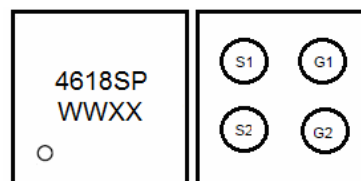
- Minimum Packing Quantity : 5,000 pcs./reel

### Application

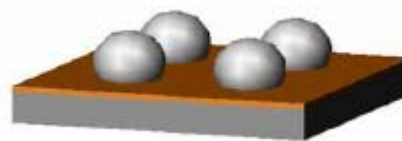
- Lithium-ion battery charging and discharging switch



### Equivalent Circuit



### Marking and pin assignment



### CSP top view

### Absolute Maximum Ratings ( $T_A = 25^\circ C$ unless otherwise noted)

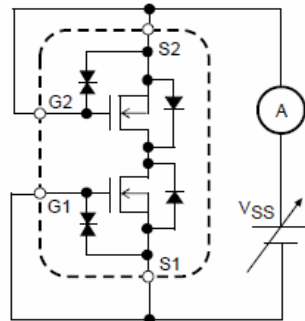
Symbol	Parameter	Limit	Unit
$V_{SSS}$	Source to Source Voltage	20	V
$V_{GSS}$	Gate-Source Voltage	$\pm 12$	V
$I_s$	Source Current(DC)	6	A
$I_{SP}$	Source Current (Pulse)	60	A
$P_T$	Total Dissipation	1.6	W
$T_{ch}$	Channel Temperature	150	$^\circ C$
$T_{STG}$	Storage Temperature	-55 To 150	$^\circ C$

**Electrical Characteristics ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)**

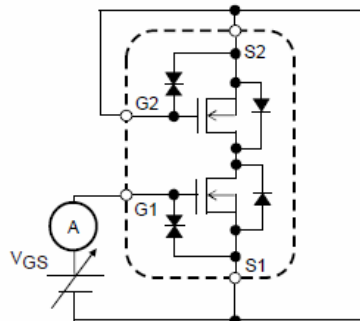
Symbol	Parameter	Condition	Min	Typ	Max	Unit
<b>Static Parameters</b>						
$BV_{SSS}$	Source to Source Breakdown Voltage	$I_S=1\text{mA}, V_{GS}=0\text{V}$ , Test Circuit 1	20	-	-	V
$I_{SSS}$	Zero- Gate Voltage Source Current	$V_{SS}=20\text{V}, V_{GS}=0\text{V}$ , Test Circuit 1	-	-	1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{SS}=0\text{V}, V_{GS}=\pm 8\text{V}$ , Test Circuit 2	-	-	$\pm 1$	$\mu\text{A}$
$V_{GS(off)}$	Cutoff Voltage	$V_{SS}=10\text{V}, I_S=1\text{mA}$ , Test Circuit 3	0.5	0.7	1.3	V
$ y_{gFs} $	Forward Transfer Admittance	$V_{SS}=10\text{V}, I_S=3\text{A}$ , Test Circuit 4	6.5	-	-	S
$R_{SS(on)}$	Static Source to Source On-Resistance	$V_{GS}=4.5\text{V}, I_S=3\text{A}$ , Test Circuit 5	11	13.6	16	$\text{m}\Omega$
		$V_{GS}=4.0\text{V}, I_S=3\text{A}$ , Test Circuit 5	11.5	14	18	$\text{m}\Omega$
		$V_{GS}=3.7\text{V}, I_S=3\text{A}$ , Test Circuit 5	12	14.2	20	$\text{m}\Omega$
		$V_{GS}=3.1\text{V}, I_S=3\text{A}$ , Test Circuit 5	12.5	15.1	23	$\text{m}\Omega$
		$V_{GS}=2.5\text{V}, I_S=3\text{A}$ , Test Circuit 5	13	16.6	25	$\text{m}\Omega$
$t_{d(on)}$	Turn-on Delay Time	$V_{SS}=10\text{V}, I_S=3\text{A}, V_{GS}=4.5\text{V}$ Test Circuit 7	-	15	-	nS
$t_r$	Turn-on Rise Time		-	50	-	nS
$t_{d(off)}$	Turn-Off Delay Time		-	40	-	nS
$t_f$	Turn-Off Fall Time		-	55	-	nS
$Q_g$	Total Gate Charge	$V_{SS}=10\text{V}, I_S=6\text{A}, V_{GS}=4.5\text{V}$ Test Circuit 8	-	25.4	-	nC
$V_{F(S-S)}$	Diode Forward Voltage	$V_{GS}=0\text{V}, I_S=6\text{A}$	-	-	1.2	V

## Test Circuit

Test Circuit 1  
 $I_{SS}$

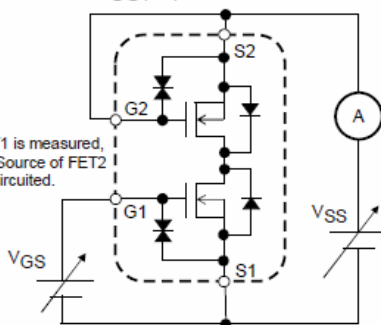


Test Circuit 2  
 $I_{GSS}$



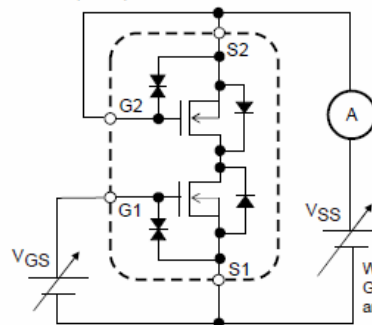
When FET1 is measured,  
Gate and Source of FET2  
are short-circuited.

Test Circuit 3  
 $V_{GS(off)}$



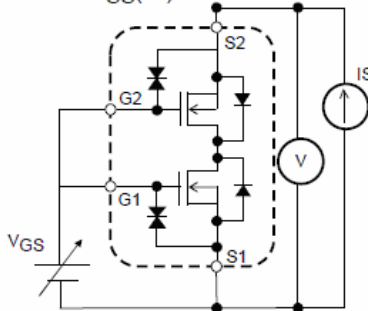
When FET1 is measured,  
Gate and Source of FET2  
are short-circuited.

Test Circuit 4  
 $|y_{fs}|$

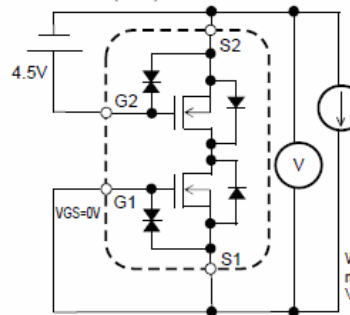


When FET1 is measured,  
Gate and Source of FET2  
are short-circuited.

Test Circuit 5  
 $R_{SS(on)}$

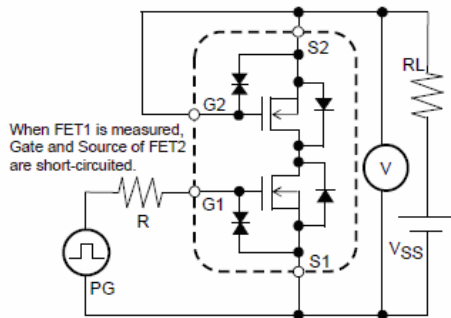


Test Circuit 6  
 $V_F(S-S)$



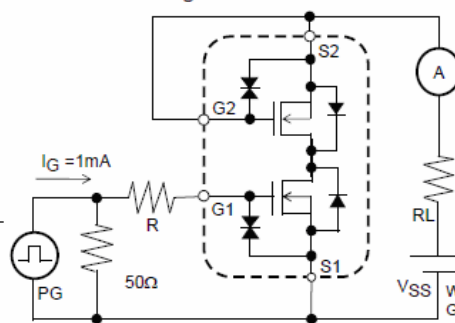
When FET1 is  
measured, +4.5V is added to  
 $V_{GS}$  of FET2.

Test Circuit 7  
 $t_d(on), t_r, t_d(off), t_f$



When FET1 is measured,  
Gate and Source of FET2  
are short-circuited.

Test Circuit 8  
 $Q_g$



When FET1 is measured,  
Gate and Source of FET2  
are short-circuited.

## Typical Electrical and Thermal Characteristics (Curves)

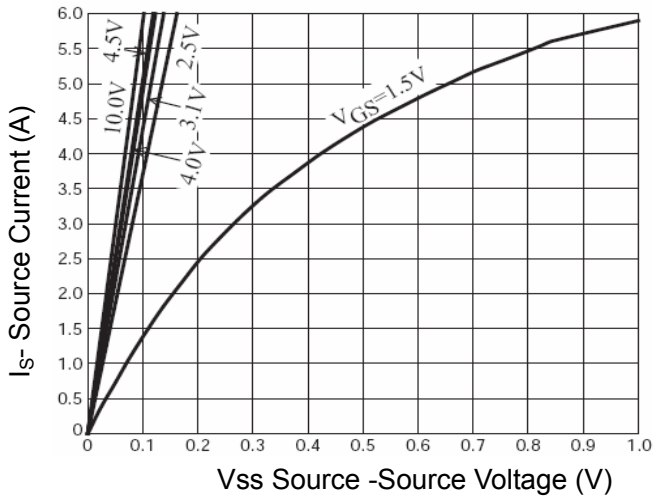


Figure 1 On-Region Characteristics

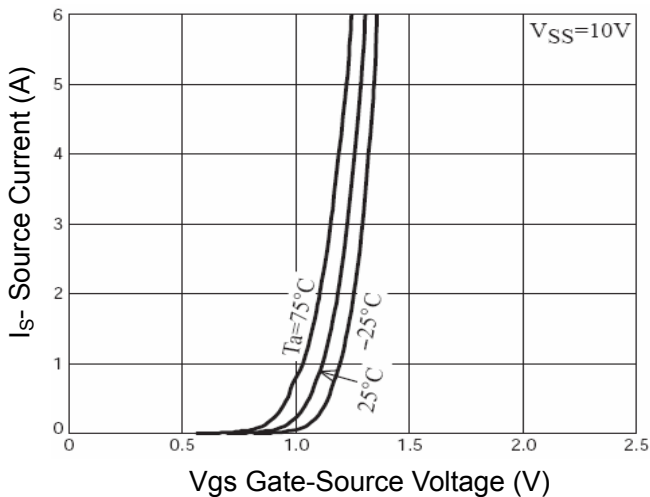


Figure 2 Transfer Characteristics

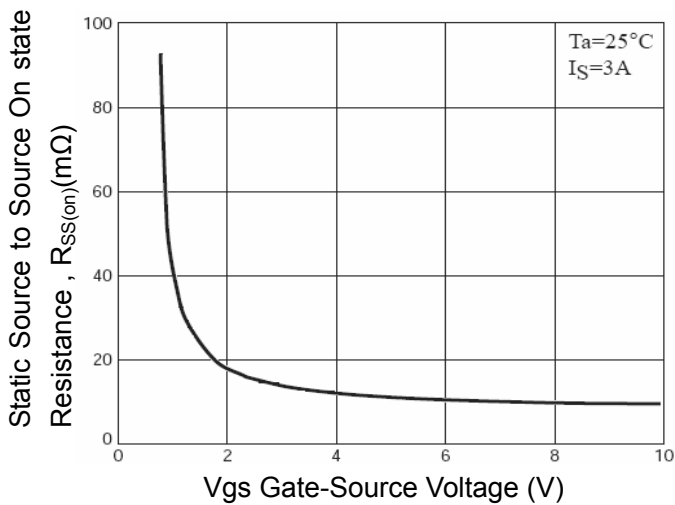


Figure 3 On-Resistance-Gate-Source Voltage

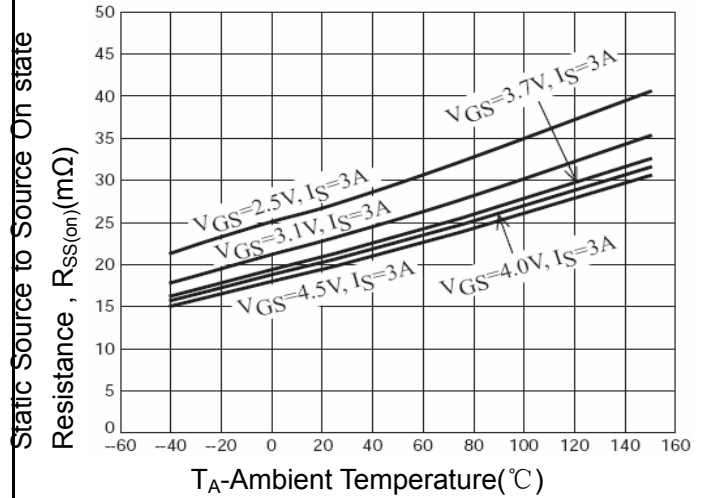


Figure 4 Rss(on)- Ambient Temperature

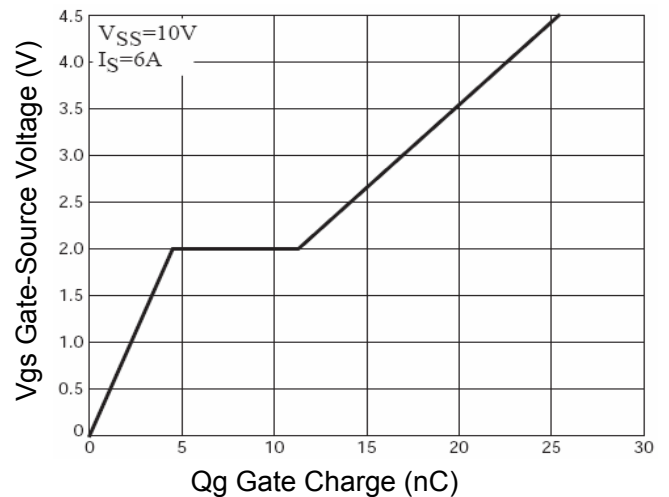


Figure 5 Gate Charge

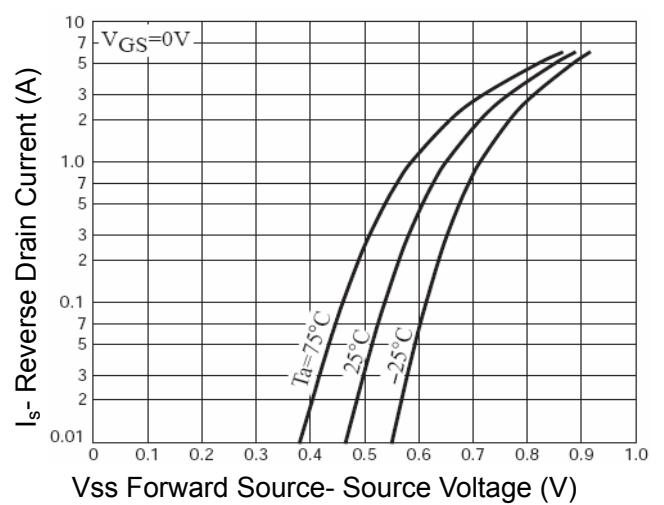


Figure 6 Body-Diode Characteristics

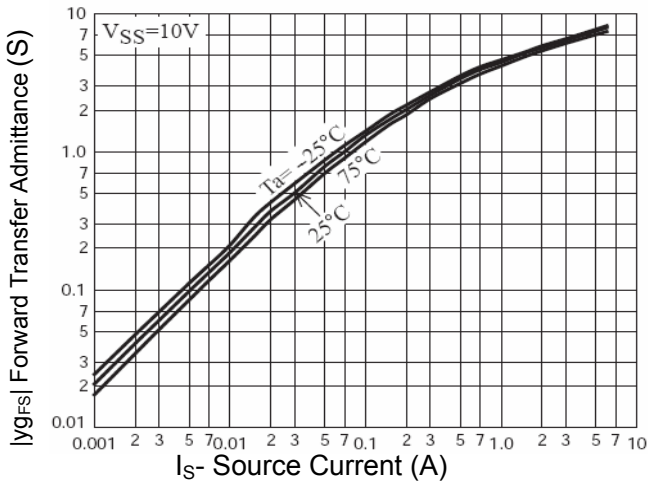


Figure 7  $|y_{fs}|$  vs  $I_S$

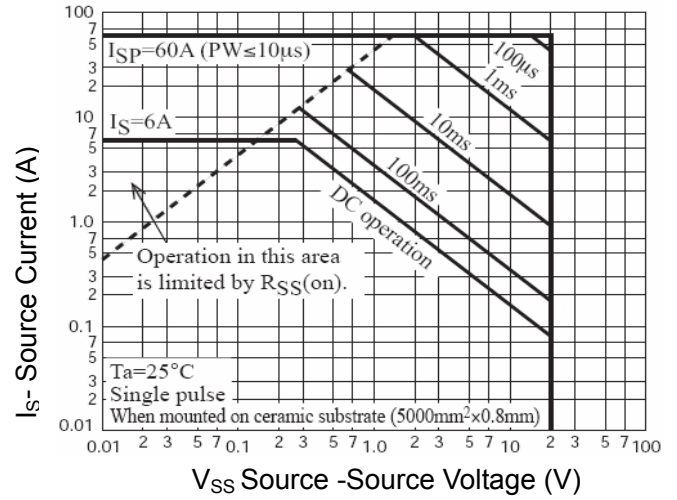


Figure 8 Safe Operation Area

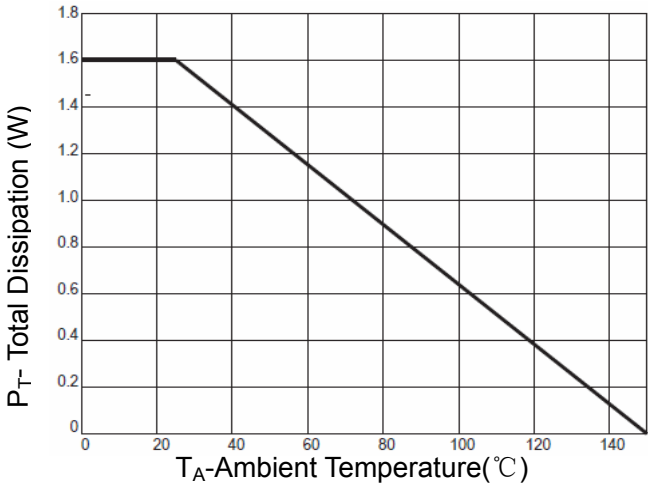


Figure 9  $P_T$  Dissipation De-rating



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